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TN3440A



NPN General Purpose Amplifier

This device is designed for use in horizontal driver, class A off-line amplifier and off-line switching applications. Sourced from Process 36.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--|-------------|-------|
| V _{CEO} | Collector-Emitter Voltage | 250 | V |
| V _{CBO} | Collector-Base Voltage | 300 | V |
| V _{EBO} | Emitter-Base Voltage | 7.0 | V |
| I _C | Collector Current - Continuous | 100 | mA |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol | Characteristic | Max | Units | |
|-----------------|--|------------|------------|--|
| | | TN3440A | | |
| P_D | Total Device Dissipation Derate above 25°C | 1.0 8.0 | W mW/°C | |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 125 | °C/W | |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 50 | °C/W | |

NPN General Purpose Amplifier

(continued)

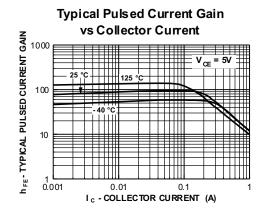
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|----------|------|--------|-------|-----|-----|-----|----|
| ectr | ıcal | ı ('h |) ara | Cto | rie | tı. | cc |
| CCL | ıvaı | | ala | CLC | | LI | LЭ |

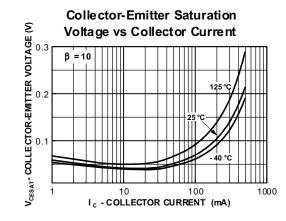
| TA = 25°C unless otherwise note | $TA = 25^{\circ}C$ | unless | otherwise | note |
|---------------------------------|--------------------|--------|-----------|------|
|---------------------------------|--------------------|--------|-----------|------|

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|------------------------------|--|--|-----|------------|-------|
| | | | | | |
| OFF CHAI | RACTERISTICS | | | | |
| $V_{CEO(sus)}$ | Collector-Emitter Sustaining Voltage* | $I_C = 50 \text{ mA}, I_B = 0$ | 250 | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | $I_C = 100 \mu A, I_E = 0$ | 300 | | V |
| I _{CEO} | Collector-Cutoff Current | V _{CE} = 200 V, I _B = 0 | | 50 | μА |
| I _{CEX} | Collector-Cutoff Current | V _{CE} = 300 V, V _{BE} = 1.5 V | | 500 | μА |
| I _{CBO} | Collector-Cutoff Current | V _{CB} = 250 V, I _E = 0 | | 20 | μА |
| I _{EBO} | Emitter-Cutoff Current | $V_{EB} = 5.0 \text{ V}, I_{C} = 0$ | | 20 | μА |
| h _{FE} | DC Current Gain | | | | |
| h _{FE} | DC Current Gain | $I_C = 2.0 \text{ mA}, V_{CE} = 10 \text{ V}$ | 30 | | |
| | | $I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 10 V | 40 | 160 | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | $I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 50 \text{ mA}, I_B = 4.0 \text{ mA}$ | 40 | 160 0.5 | V |
| | Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage | | 40 | | V |
| V _{CE(sat)} | , and the second | I _C = 50 mA, I _B = 4.0 mA | 40 | 0.5 | |
| V _{BE(sat)} | , and the second | $I_{\rm C}$ = 50 mA, $I_{\rm B}$ = 4.0 mA | 40 | 0.5 | |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | $I_{\rm C}$ = 50 mA, $I_{\rm B}$ = 4.0 mA | 15 | 0.5 | |
| $V_{BE(SAT)}$ SMALL SI f_T | Base-Emitter Saturation Voltage GNAL CHARACTERISTICS | I_C = 50 mA, I_B = 4.0 mA I_C = 50 mA, I_B = 4.0 mA | | 0.5 | V |
| | Base-Emitter Saturation Voltage GNAL CHARACTERISTICS Current Gain - Bandwidth Product | I_C = 50 mA, I_B = 4.0 mA I_C = 50 mA, I_B = 4.0 mA I_C = 10 mA, I_C = 10 V, I_C = 1.0 MHz | | 0.5 | V |

^{*}Pulse Test: Pulse Width $\leq\!300~\mu\text{s}$, Duty Cycle $\leq\!1.0\%$

Typical Characteristics

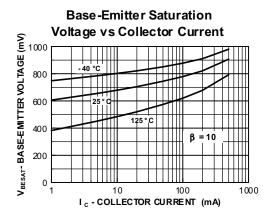


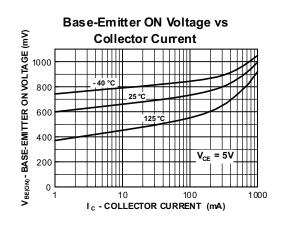


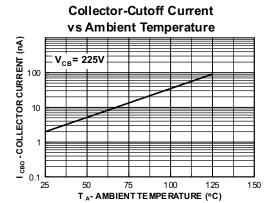
NPN General Purpose Amplifier

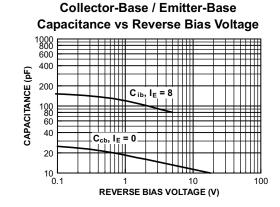
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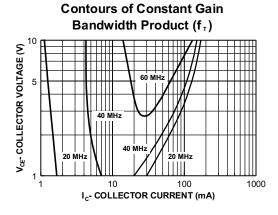
Typical Characteristics (continued)

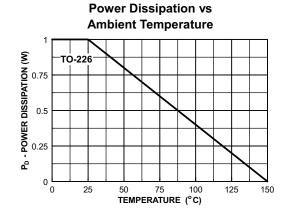


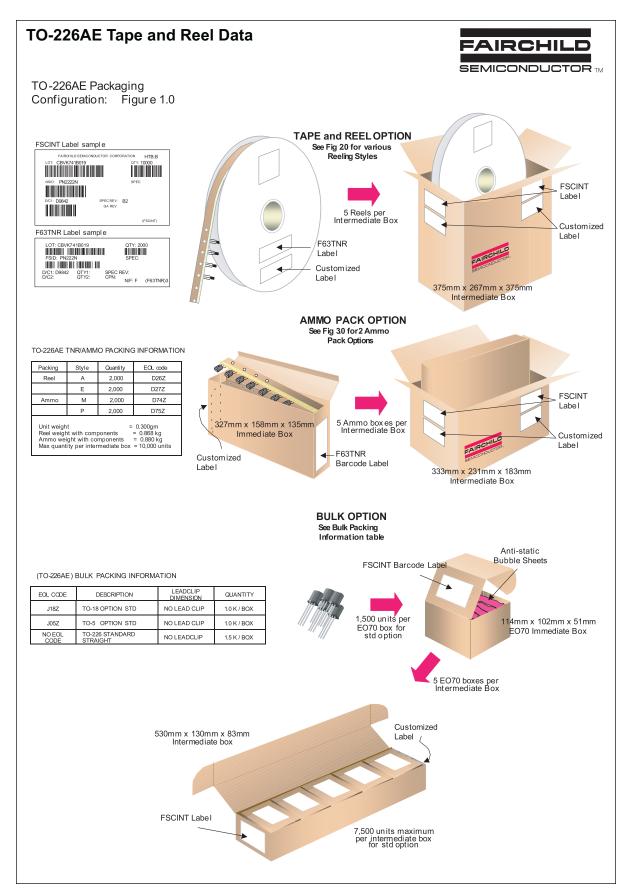








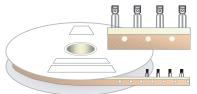




TO-226AE Tape and Reel Data, continued

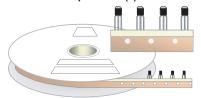
TO-226AE Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A" D26Z, D70Z (s/h)

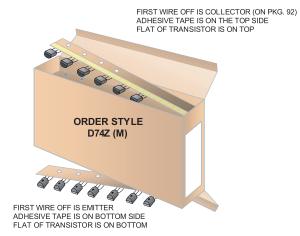
Machine Option "E"(J)



Style "E" D27Z, D71Z (s/h)

TO-226AE Radial Ammo Packaging

Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92)
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON BOTTOM

ORDER STYLE
D75Z (P)

FIRST WIRE OFF IS COLLECTOR ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

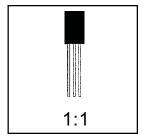
TO-226AE Tape and Reel Data, continued TO-226AE Tape and Reel Taping Dimension Configuration: Figure 4.0 ITEM DESCRIPTION SYMBOL DIMENSION Base of Package to Lead Bend 0.098 (max) Component Height Hb 1.078 (+/- 0.050) User Direction of Feed Lead Clinch Height 0.630 (+/- 0.020) HO Component Base Height H1 0.748 (+/- 0.020) Component Alignment (side/side) Pd 0.040 (max) 0.031 (max) Component Alignment (front/back) Hd Component Pitch 0.500 (+/- 0.020) РО Feed Hole Pitch 0.500 (+/- 0.008) Hole Center to First Lead P1 0.150 (+0.009, -0.010) Hole Center to Component Center P2 0.247 (+/- 0.007) Lead Spread F1/F2 0.104 (+/- 0 010) Lead Thickness d 0.018 (+0.002, -0.003) 0.429 (max) Cut Lead Length L1 0.209 (+0.051, -0.052) Taped Lead Length Taped Lead Thickness 0.032 (+/- 0.006) Carrier Tape Thickness t1 0.021 (+/- 0.006) TO-226AE Reel 0.708 (+0.020, -0.019) Carrier Tape Width W Configuration: Figure 5.0 Hold - down Tape Width wo 0.236 (+/- 0.012) 0.035 (max) Hold - down Tape position W1 0.360 (+/- 0.025) Feed Hole Position W2 0.157 (+0.008, -0.007) DO Sprocket Hole Diameter Lead Spring Out S 0.004 (max) Note: All dmensions are in inches. D4 ITEM DESCRIPTION SYMBOL MINIMUM MAXIMUM Red Diameter 13975 14.025 Arbor Hole Diameter (Standard) 1.160 1.200 D2 D2 0.650 0.700 (Small Hole) Core Diameter D3 3.100 3.300 Hub Recess Inner Diameter 2.700 3.100 D4 Hub Recess Depth W 1 0.370 0.570 Range to Range Inner Width 1.630 Hub to Hub Center Width 2.090 Note: All dimensions are inches

TO-226AE Package Dimensions



TO-226AE (FS PKG Code 95, 99)



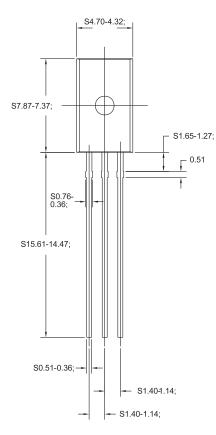


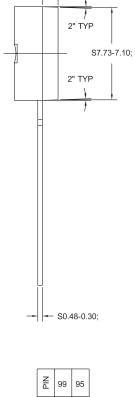
Scale 1:1 on letter size paper

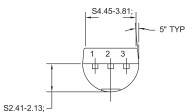
Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.300

- S1.52-1.02;







For leadformed option ordering, refer to Tape & Reel data information.

1 E E 2 B C 3 C B TO-226AE (95,99)

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